

1SS357

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Features

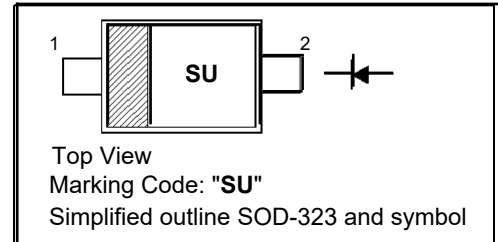
- Low forward voltage
- Low reverse current

Applications

- High Speed Switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Average Forward Current	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current	I_{FM}	300	mA
Surge Forward Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^{\circ}\text{C}$

Characteristics at $T_a = 25^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	0.6	V
Reverse Current at $V_R = 40\text{ V}$	I_R	5	μA
Total Capacitance at $V_R = 0, f = 1\text{ MHz}$	C_T	25	pF

Typical Characteristics

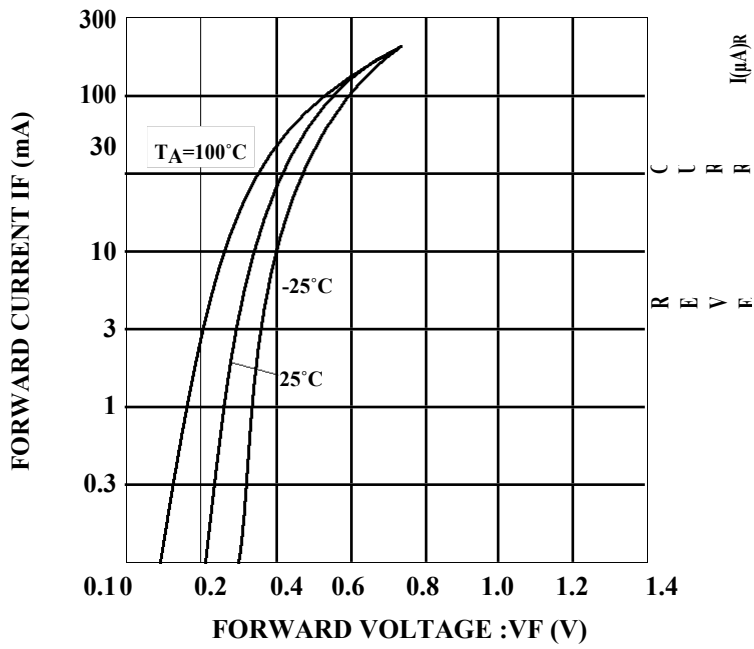


Fig.1 Forward Characteristics

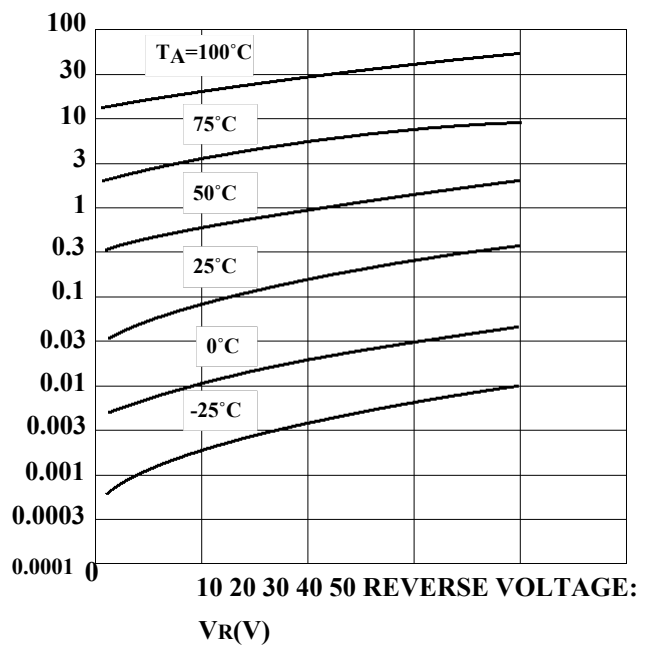


FIG.2 Reverse Characteristics

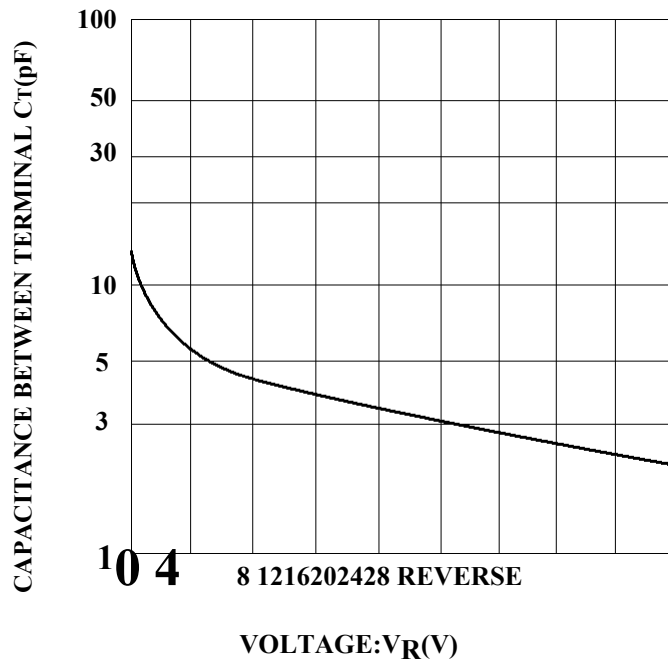
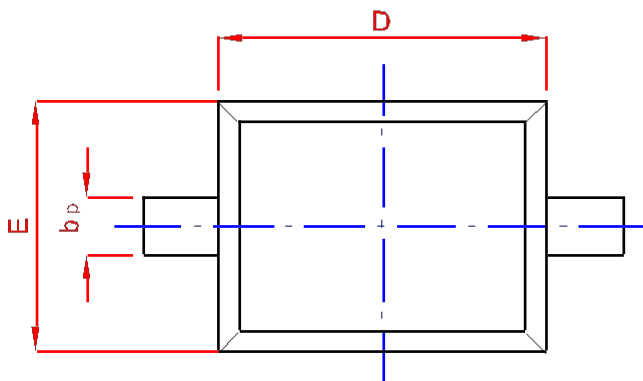
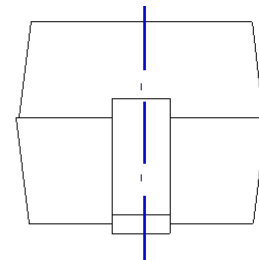
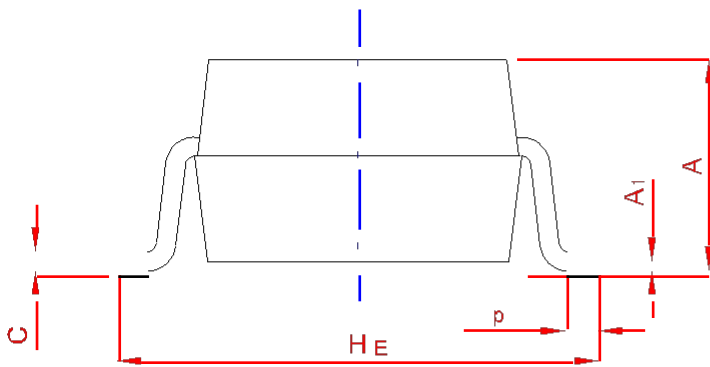
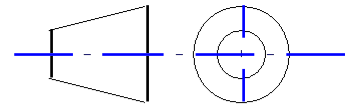


FIG.3 Capacitance Between Terminal Characteristics

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	bp	C	D	E	HE	A1	Lp
mm	1.20	0.40	0.15	1.80	1.35	2.80	0.10	0.50
	0.90	0.25	0.10	1.60	1.15	2.30	0.01	0.20